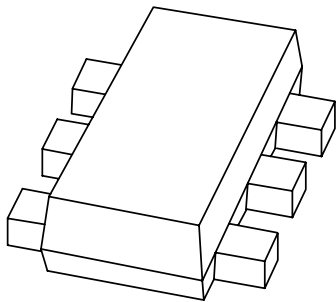


# DATA SHEET



## **PBSS2515VS**

15 V low  $V_{CE(sat)}$  NPN double  
transistor

Product data sheet  
Supersedes data of 2001 Nov 07

2004 Dec 23

# 15 V low $V_{CE(sat)}$ NPN double transistor

# PBSS2515VS

### FEATURES

- 300 mW total power dissipation
- Very small 1.6 × 1.2 mm ultra thin package
- Excellent coplanarity due to straight leads
- Low collector-emitter saturation voltage
- High current capability
- Improved thermal behaviour due to flat lead
- Replaces two SC-75/SC-89 packaged low  $V_{CEsat}$  transistors on same PCB area
- Reduces required PCB area
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and muting
- Low frequency driver circuits
- LCD backlighting
- Audio frequency general purpose amplifier applications
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

### DESCRIPTION

NPN low  $V_{CEsat}$  double transistor in a SOT666 plastic package.  
 PNP complement: PBSS3515VS.

### MARKING

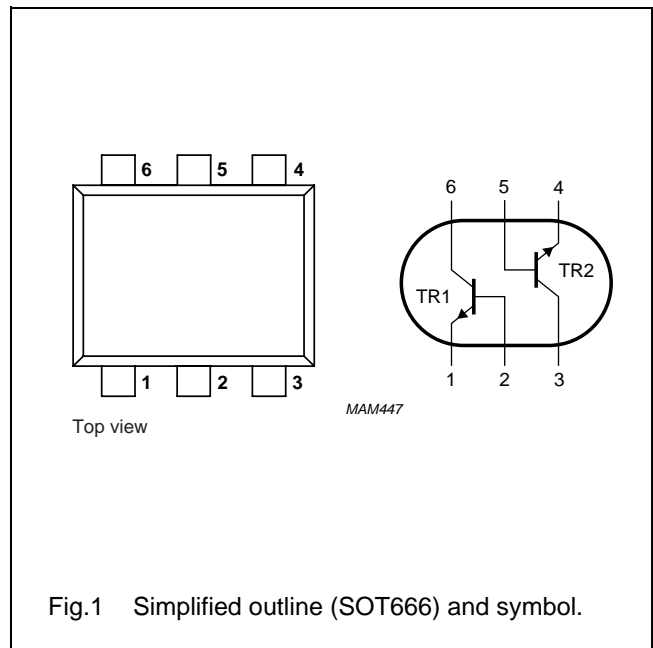
TYPE NUMBER	MARKING CODE
PBSS2515VS	N9

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	15	V
$I_{CM}$	peak collector current	1	A
$R_{CEsat}$	equivalent on-resistance	<500	m $\Omega$

### PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2



### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS2515VS	–	plastic surface mounted package; 6 leads	SOT666

15 V low  $V_{CE(sat)}$  NPN double transistor

PBSS2515VS

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor unless otherwise specified</b>					
$V_{CBO}$	collector-base voltage	open emitter	–	15	V
$V_{CEO}$	collector-emitter voltage	open base	–	15	V
$V_{EBO}$	emitter-base voltage	open collector	–	6	V
$I_C$	collector current (DC)		–	500	mA
$I_{CM}$	peak collector current		–	1	A
$I_{BM}$	peak base current		–	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	200	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C
<b>Per device</b>					
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	300	mW

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

**Notes**

1. Transistor mounted on an FR4 printed-circuit board.
2. The only recommended soldering method is reflow soldering.

15 V low  $V_{CE(sat)}$  NPN double transistor

## PBSS2515VS

**CHARACTERISTICS**

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

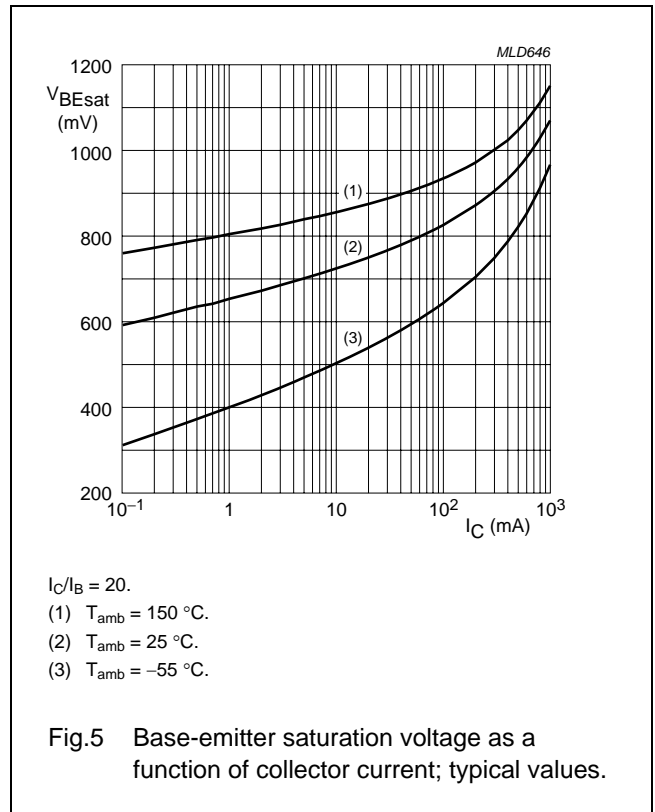
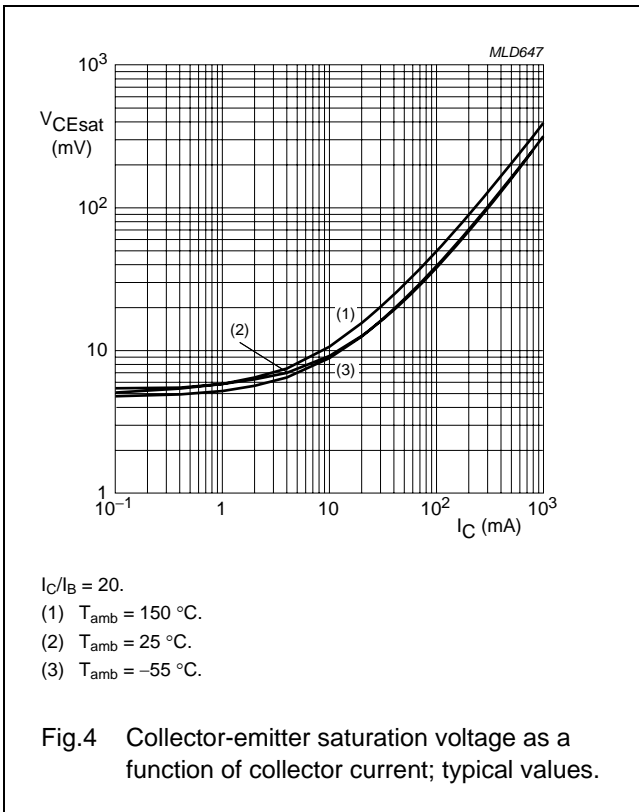
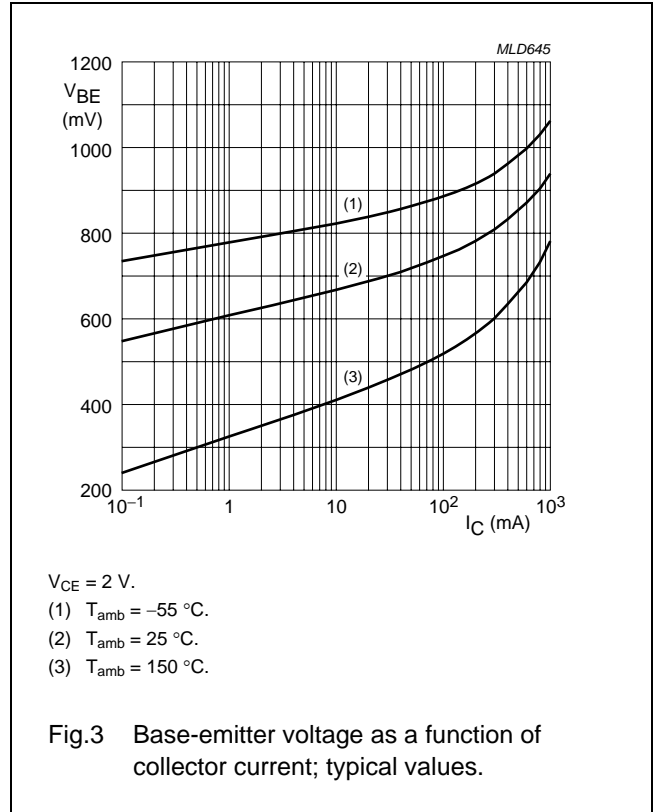
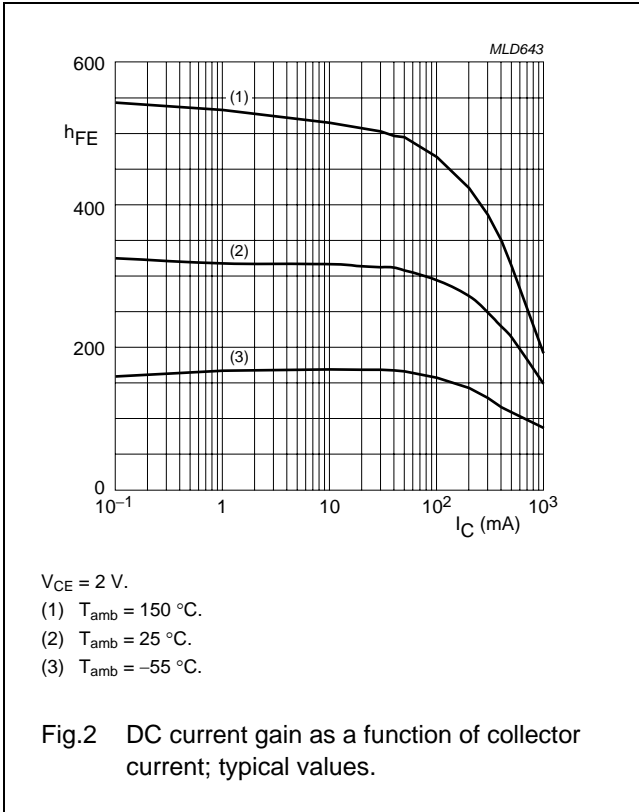
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Per transistor unless otherwise specified</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 15\text{ V}; I_E = 0\text{ A}$	–	–	100	nA
		$V_{CB} = 15\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ °C}$	–	–	50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	–	–	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 2\text{ V}; I_C = 10\text{ mA}$	200	–	–	
		$V_{CE} = 2\text{ V}; I_C = 100\text{ mA};$ note 1	150	–	–	
		$V_{CE} = 2\text{ V}; I_C = 500\text{ mA};$ note 1	90	–	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	–	25	mV
		$I_C = 200\text{ mA}; I_B = 10\text{ mA}$	–	–	150	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA};$ note 1	–	–	250	mV
$R_{CEsat}$	equivalent on-resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA};$ note 1	–	300	<500	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 50\text{ mA};$ note 1	–	–	1.1	V
$V_{BE}$	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 100\text{ mA};$ note 1	–	–	0.9	V
$f_T$	transition frequency	$I_C = 100\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	250	420	–	MHz
$C_C$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	–	4.4	6	pF

**Note**

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .

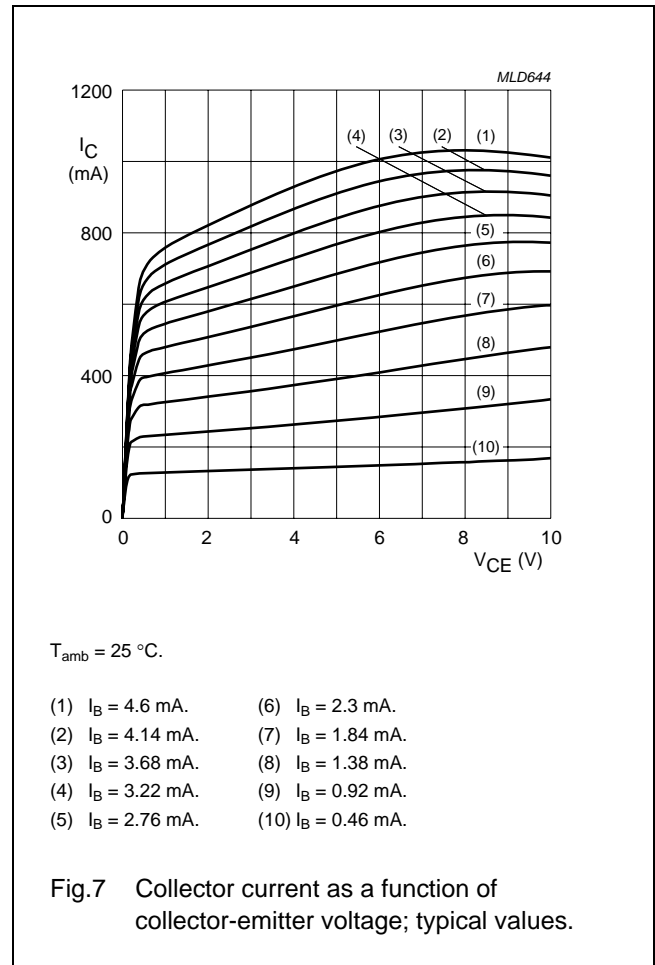
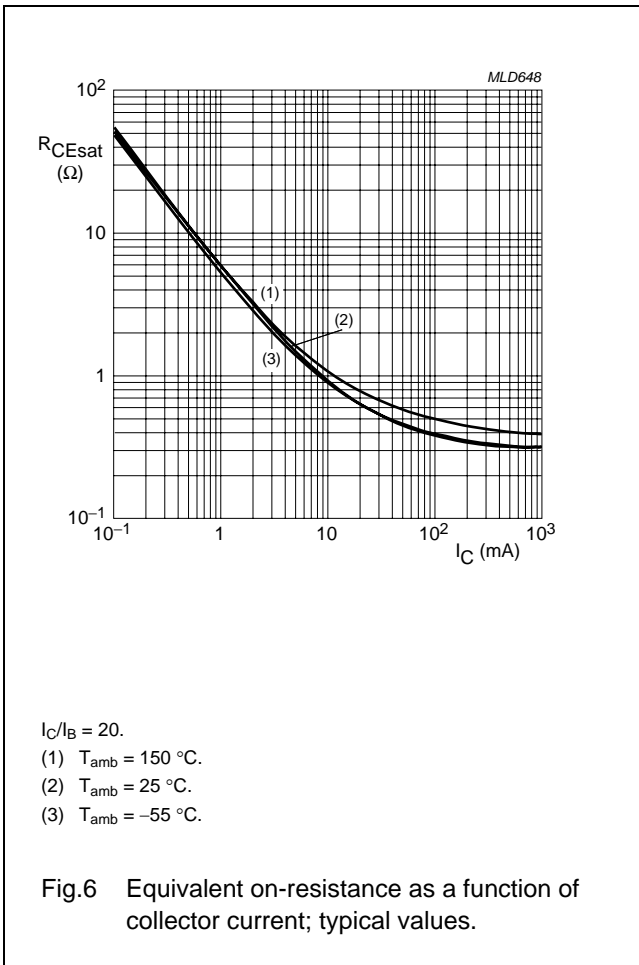
15 V low  $V_{CE(sat)}$  NPN double transistor

PBSS2515VS



15 V low  $V_{CE(sat)}$  NPN double transistor

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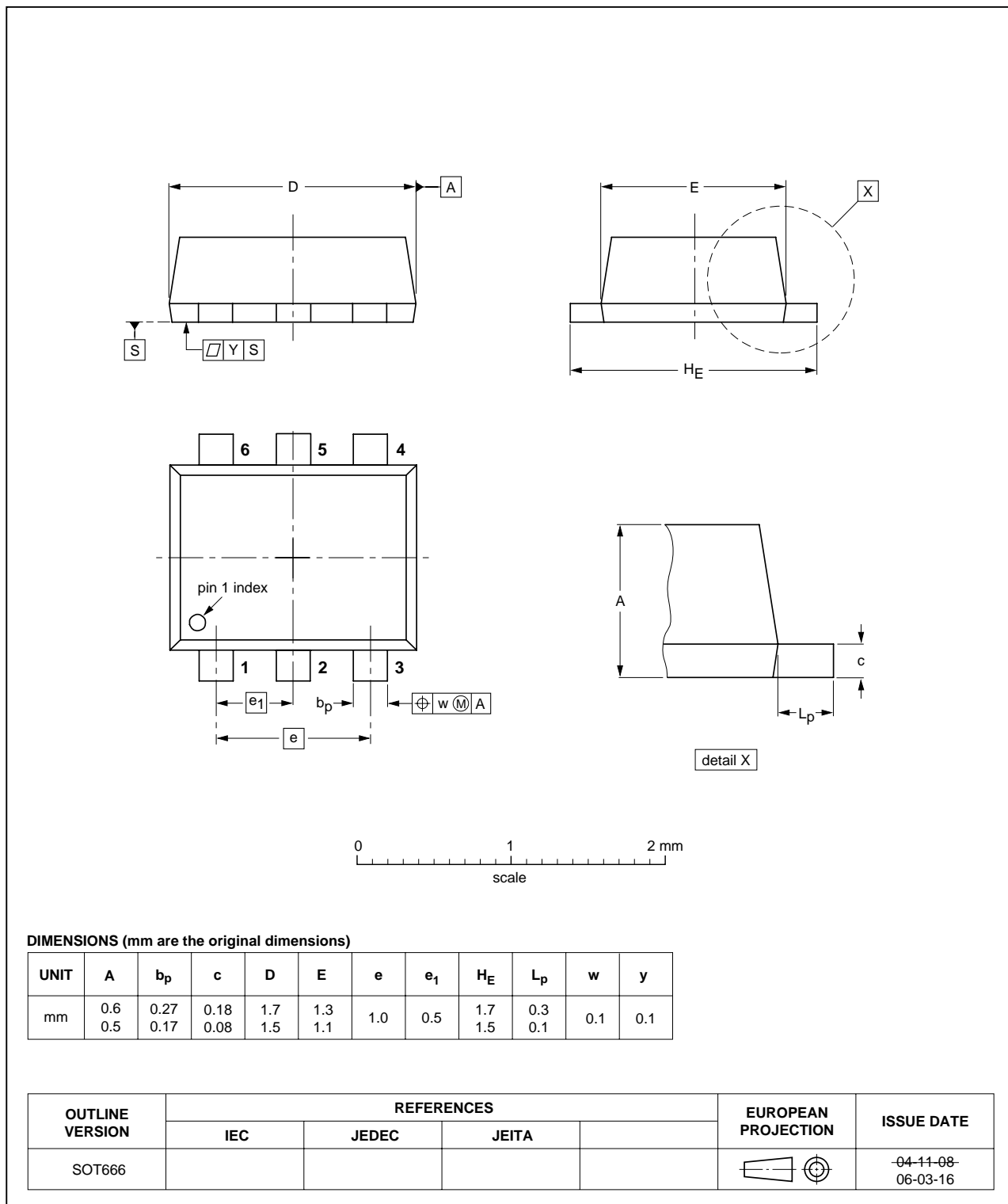
15 V low  $V_{CE(sat)}$  NPN double transistor

PBSS2515VS

PACKAGE OUTLINE

Plastic surface-mounted package; 6 leads

SOT666



15 V low  $V_{CE(sat)}$  NPN double transistor

PBSS2515VS

**DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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# ***NXP Semiconductors***

## **Customer notification**

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## **Contact information**

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